Pictures to: 3.4.1 Weak Beam Contrast of Stacking Faults in TEM

The set o f pictures contained in the publication follows:

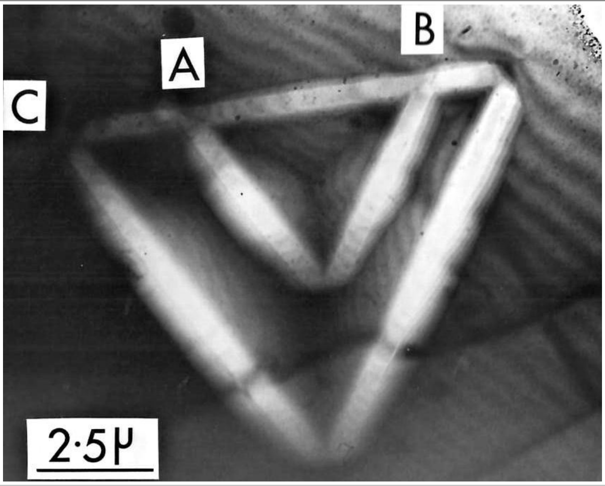


Fig. 1. 1.
Low magnification micrograph of the stacking faults in silicon which are studied in detail.

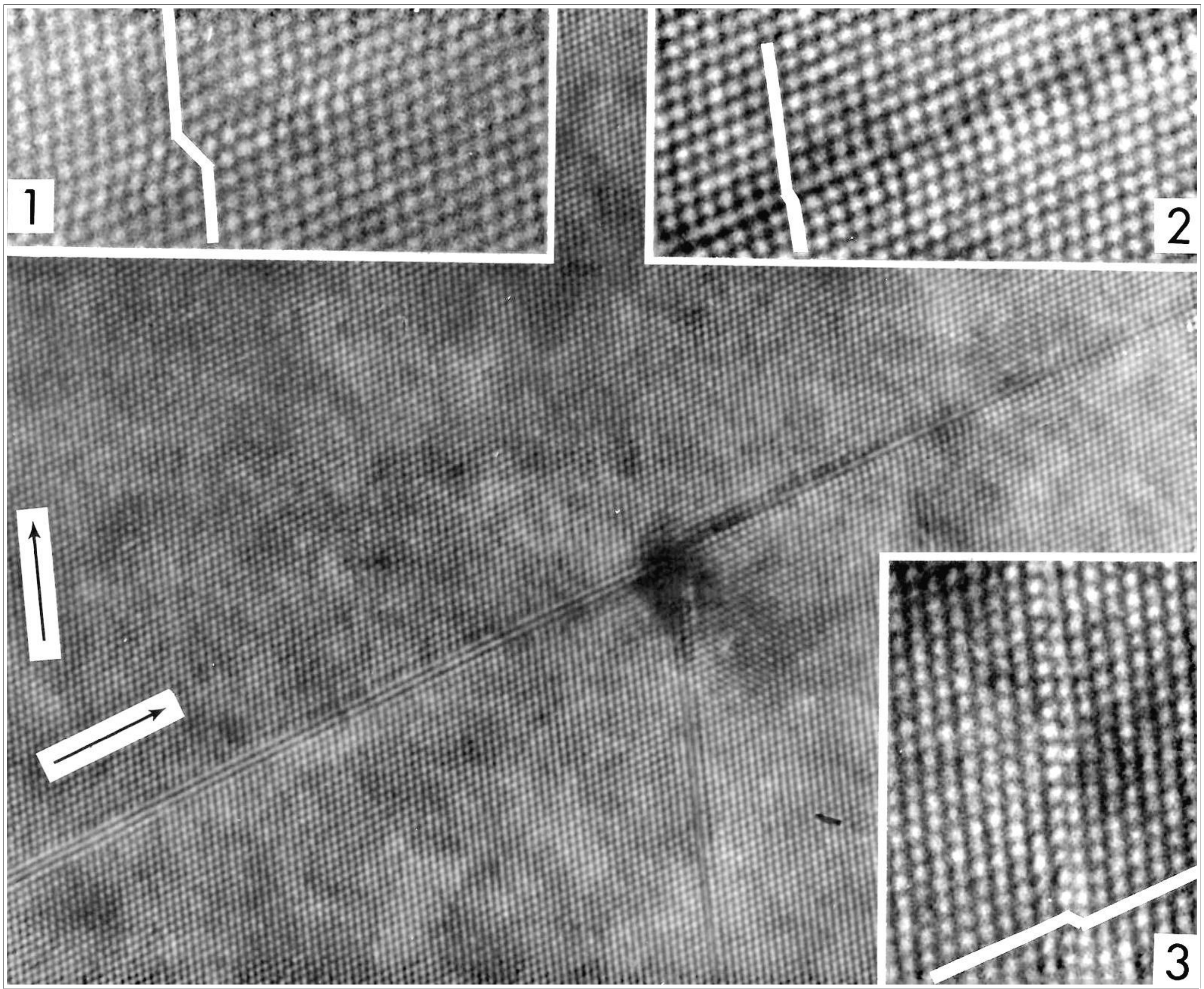
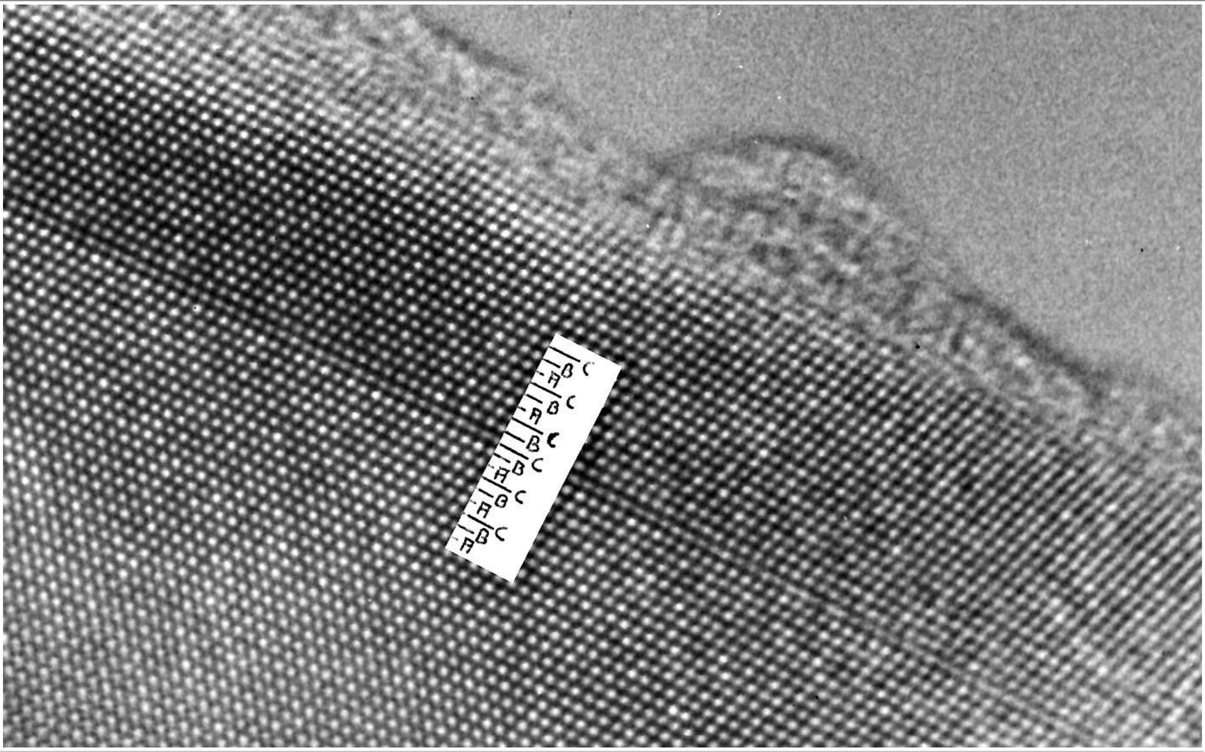
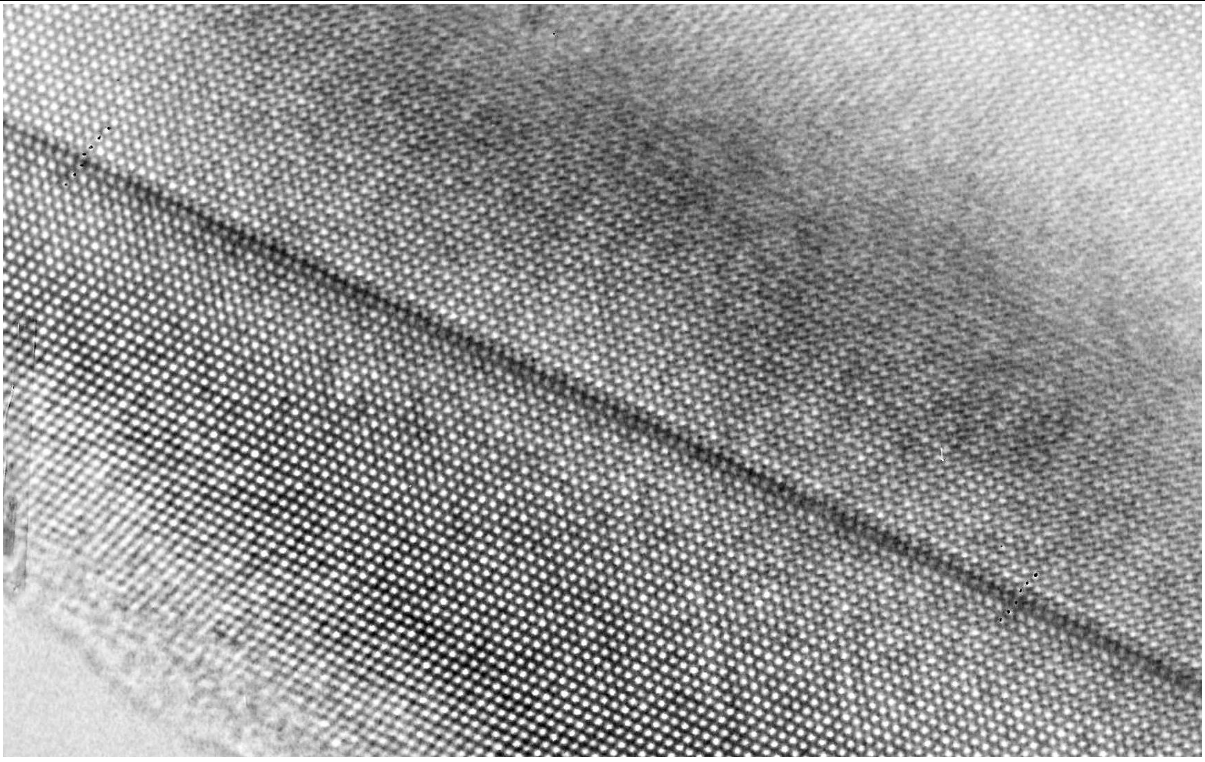


Fig. 2 .
Lattice image of stacking faults at area B in Fig. 1. Alrrows denote traces of {111} planes.



Auxiliary picture to Fig Fig. 2
Showing parts of the stacking fault and illustrating the resolution one could achieve with the Elmiskop 102



As above; auxililiary picture to Fig. 2

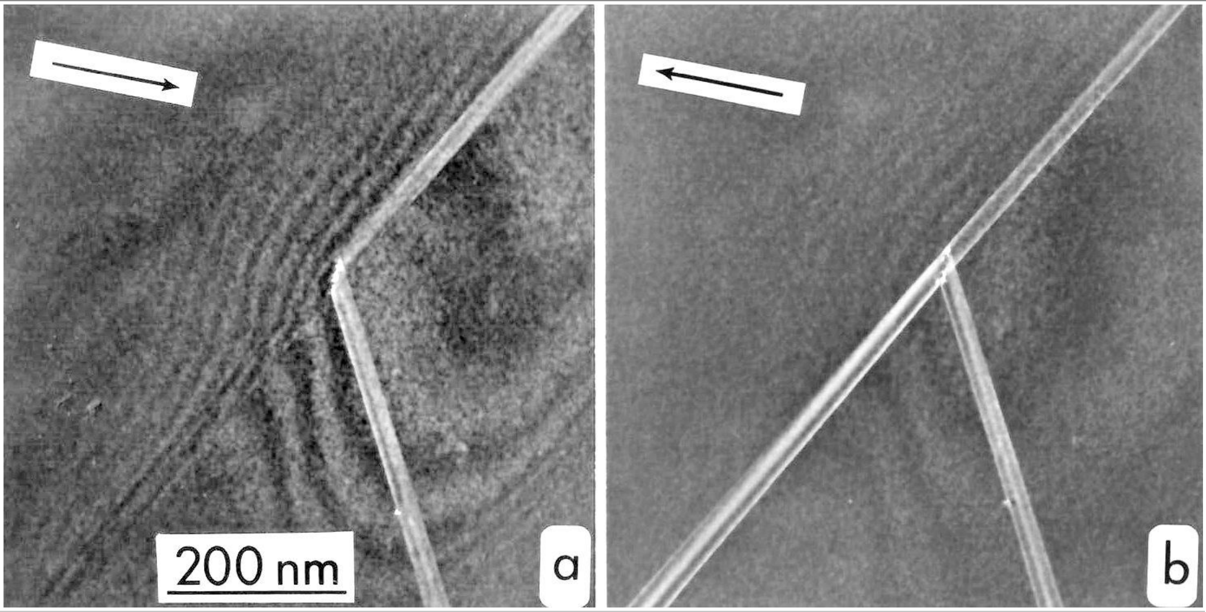


Fig. 3 .
Weak·beam image of area B. Arrows in this and in the following pictures indicate diffraction vectors. g={220} in this case

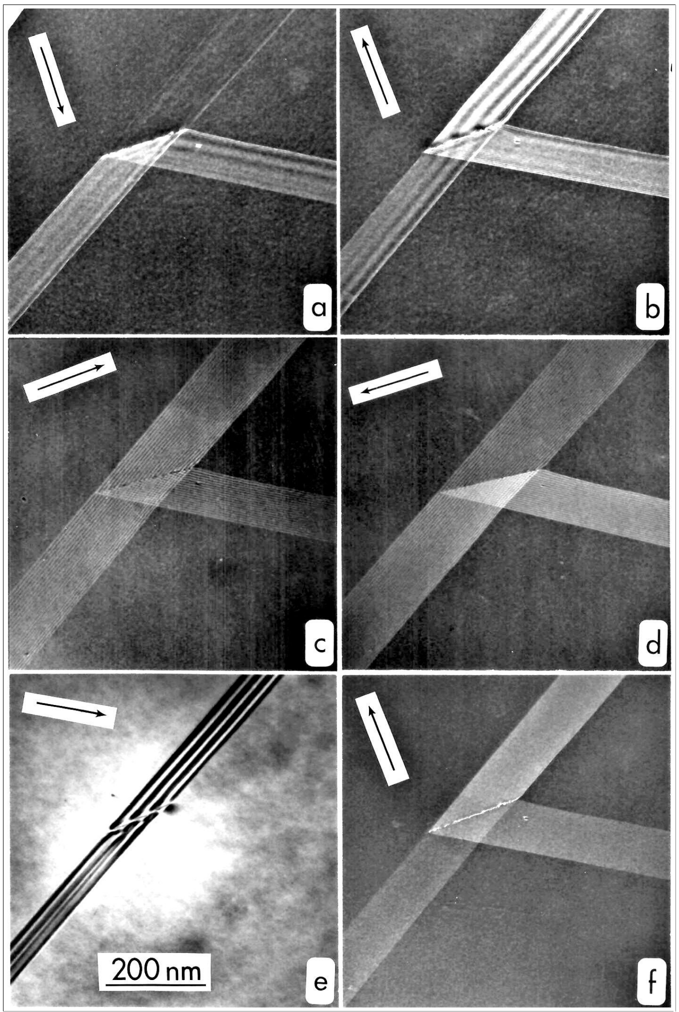


Fig. 4 .
Area A imaged with different diffraction vectors. a), b), c), f): g={220}, c), d): g={lll}. For details see text

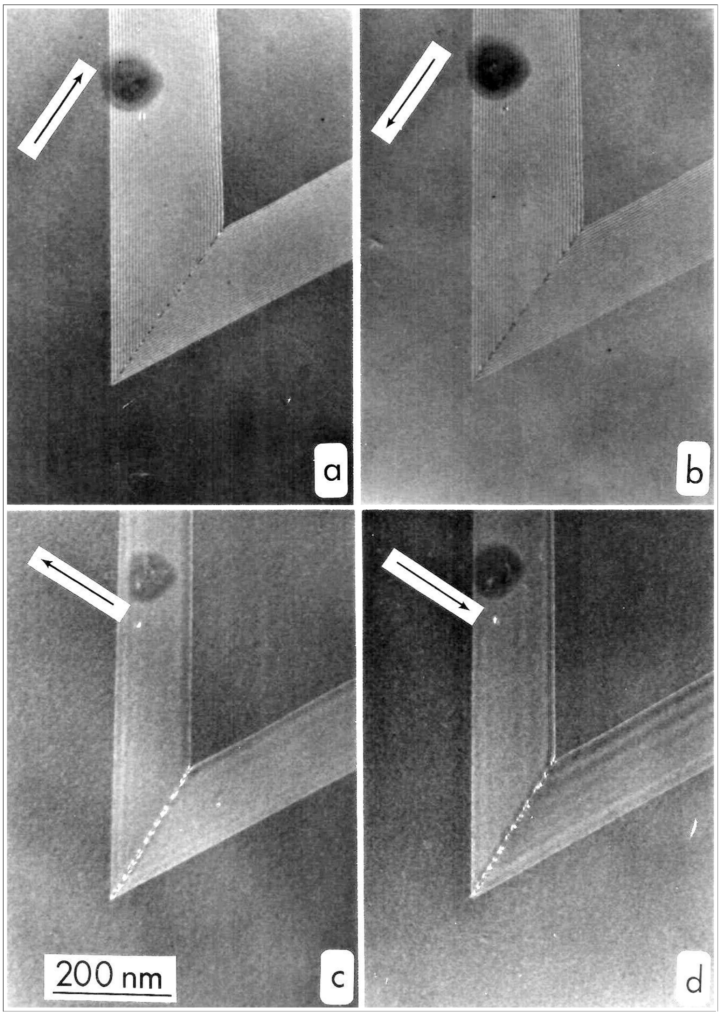


Fig. 5.
Area C imaged with different diffraction vectors. a), b): y={lll};
cl, d): g={220}

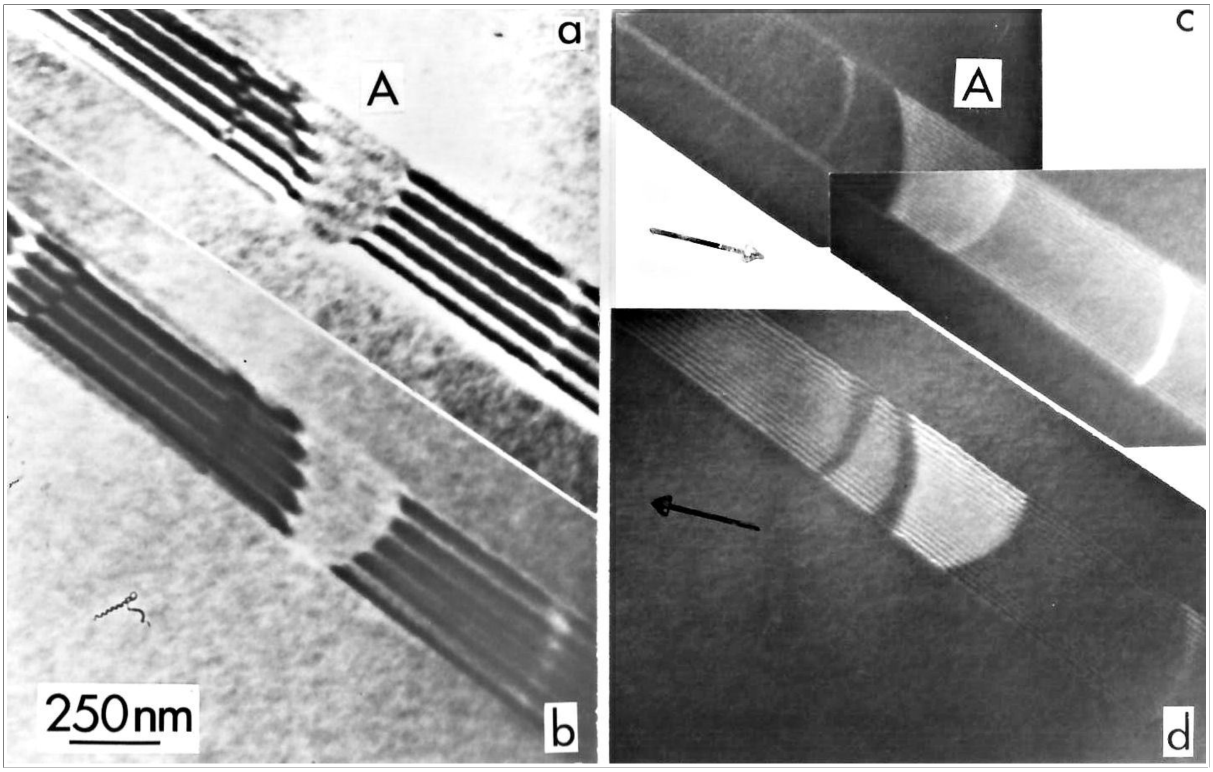


Fig. 6 This is a picture from B. Carter.
Overlapping stacking faults in stainies steel. The small arrows mark identical areas; g={lll}

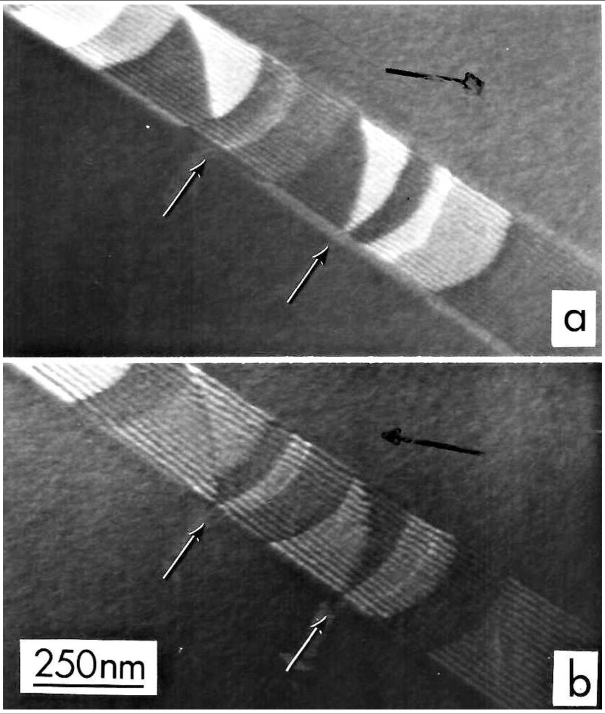


Fig. 7.
This is a picture from B. Carter.
Overlapping stacking faults in stainless steel. The small arrows mark identical areas; g={Ill}

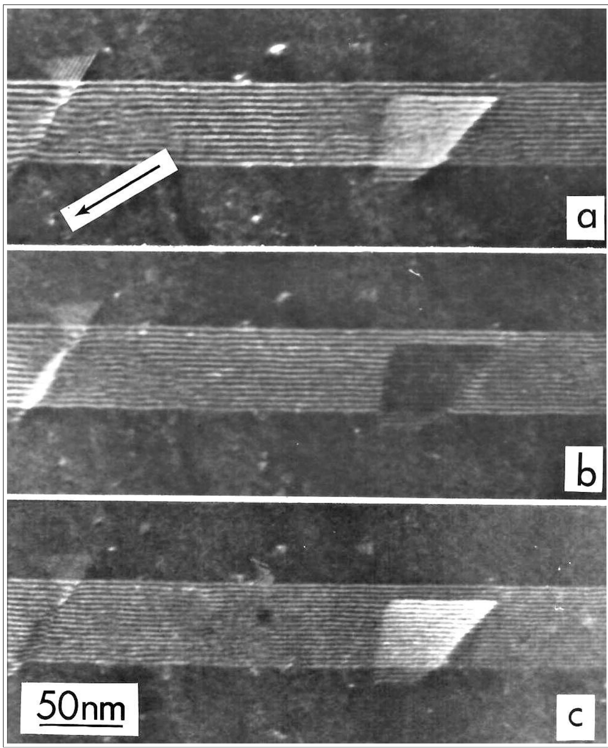


Fig. 8.
This is a picture from B. Carter.
Overlapping stacking faults in CuAI alloy. The magnitude of the excitation error s increases from a) to c; G={lll}

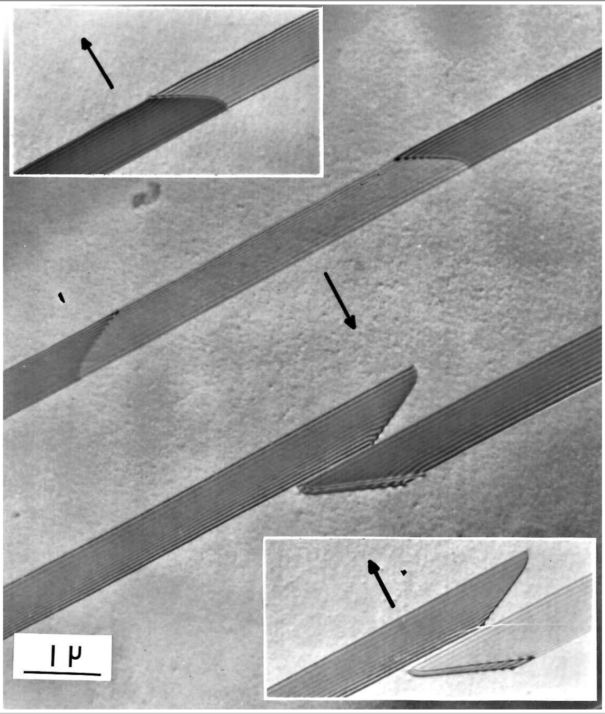


Fig. 9.
This is a picture from B. Carter.
Overlapping stacking faults in Si. A significant contrast change is visible upon reversing the sign of g={220} as shown in the inserts